Ferroelectric Memories

Density (Bit)	Part No.	Bit configuration (Word×Bit)	Supply voltage (V)	Operating voltage		Current consumption(Max.)		Write cycle time (Max.) (ms)	Operating temp (°C)	Rewrite capability (times)	Data retention (Year)	Package
				Read (V)	Write (V)	Active (μA)	Stand-by (μA)					
New 16K	**BR24CF16F**	2,048×8	5	4.5~5.5	4.5~5.5	100	25	0	-40~85	10^{12}	10	SOP8

EEPROM

●3 wire serial

Density (Bit)	Part No.	Bit configuration (Word×Bit)	Supply voltage (V)	Operating voltage		Current consumption(Max.)		Write cycle time (Max.) (ms)		Operating temp (°C)	Rewrite capability (times)	Data retention (Year)	Package
				Read (V)	Write (V)	Active (mA)	Stand-by (μA)		Vcc				
1K	**BR93LL46F/FV**	64×16	2	1.8~4.0	1.8~4.0	2	1	25	2V	-40~85	10^5	10	SOP8/SSOP-B8
	BR93LC46/F/FV		3	2.0~5.5	2.7~5.5	2	3	25	3V				DIP8/SOP8/SSOP-B8
	BR93LC46A/AF		5	2.0~5.5	4.5~5.5	3	5	10	5V				DIP8/SOP8
2K	**BR93LC56/F/FV**	128×16	3	2.0~5.5	2.7~5.5	2	3	25	3V				DIP8/SOP8/SSOP-B8
	BR93LC56A/AF		5	2.0~5.5	4.5~5.5	3	5	10	5V				DIP8
4K	**BR93LC66/RF**	256×16	3	2.0~5.5	2.7~5.5	2	3	25	3V				SOP8
	BR93LC66A/ARF		5	2.0~5.5	4.5~5.5	3	5	10	5V				

Note: ☆:Under development

●3 wire serial (Direct connection serial port)

Density (Bit)	Part No.	Bit configuration (Word×Bit)	Supply voltage (V)	Operating voltage		Current consumption(Max.)		Write cycle time (Max.) (ms)		Operating temp (°C)	Rewrite capability (times)	Data retention (Year)	Package
				Read (V)	Write (V)	Active (mA)	Stand-by (μA)		Vcc				
2K	**BR9020/F**	128×16	3~5	2.0~5.5	2.7~5.5	1.5 2	2 3	15 10	3V 5V	-40~85	10^5	10	DIP8 SOP8
4K	**BR9040/F**	256×16	3~5	2.0~5.5	2.7~5.5	1.5 2	2 3	15 10	3V 5V				

●2 wire serial (I^2C BUS Type)

Density (Bit)	Part No.	Bit configuration (Word×Bit)	Supply voltage (V)	Operating voltage		Current consumption(Max.)		Write cycle time (Max.) (ms)		Operating temp (°C)	Rewrite capability (times)	Data retention (Year)	Package
				Read (V)	Write (V)	Active (mA)	Stand-by (μA)		Vcc				
1K	**BR24C01A/AF**	128×8	3~5	2.7~5.5	2.7~5.5	1	2	25 10	3V 5V	-40~85	10^5	10	DIP8 SOP8
2K	**BR24C02/F**	256×8	3~5	2.7~5.5	2.7~5.5	1	2	25 10	3V 5V				
4K	**BR24C04/F**	512×8	3~5	2.7~5.5	2.7~5.5	1	2	25 10	3V 5V				

Note : I^2C BUS is a registered trademark of Philips.

●Parallel (CMOS Type)

Density (Bit)	Part No.	Bit configuration (Word×Bit)	Access time Max. (ns)	Supply voltage (V)	Operating voltage		Current consumption(Max.)		Operating temp (°C)	Rewrite capability (ten thousand times)	Data retention (Year)	Package
					Read (V)	Write (V)	Active (mA)	Stand-by (μA)				
16K	**BR28C16A-150**	2K×8	150	5	4.5~5.5	4.5~5.5	30	0.1	0~70	10^4	10	DIP24

SRAM

Density (Bit)	Part No.	Bit configuration (Word×Bit)	Access time Max. (ns)	Supply voltage (V)	Current consumption(Max.)			Package
					Active (mA)	Stand-by (μA)		
						Vcc=5V	Vcc=3V	
64K	**BR6265BF-N10SL**	8K ×8	100	5	40	20	10	SOP-N28(450mil)
New 256K	**BR62256F-70LL**	32K ×8	70	5	45	50	20	SOP-N28(450mil)

Memory Backup IC

Part No.	Supply voltage (V)	Output voltage (backup) (V)	Current consumption (backup) (μA)	Detect voltage (V)	Switching voltage (V)	Features	Package
BA6129AF	5	4.95	0.5	3.5	3.3	Outputs CS, CSB, and reset signals below detect or voltage	SOP8
BA6162/F	5	4.95	0.5	4.2	3.3	Same as BA6129AF but different detector voltage	DIP8/SOP8